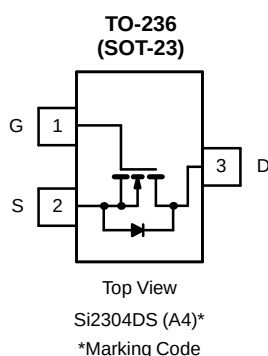




N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.117 @ $V_{GS} = 10$ V	2.5
	0.190 @ $V_{GS} = 4.5$ V	2.0



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	2.5	A
	$T_A = 70^\circ\text{C}$		2.0	
Pulsed Drain Current ^b		I_{DM}	10	
Continuous Source Current (Diode Conduction) ^a		I_S	1.25	W
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	1.25	
	$T_A = 70^\circ\text{C}$		0.80	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	100	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^c		166	

Notes

- Surface Mounted on FR4 Board, $t \leq 5$ sec.
- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

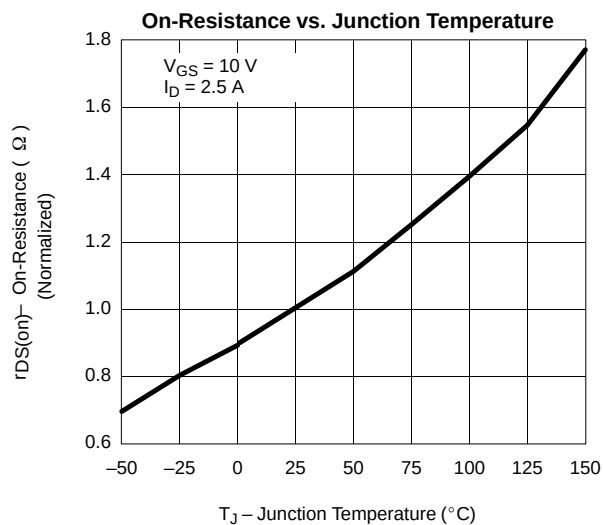
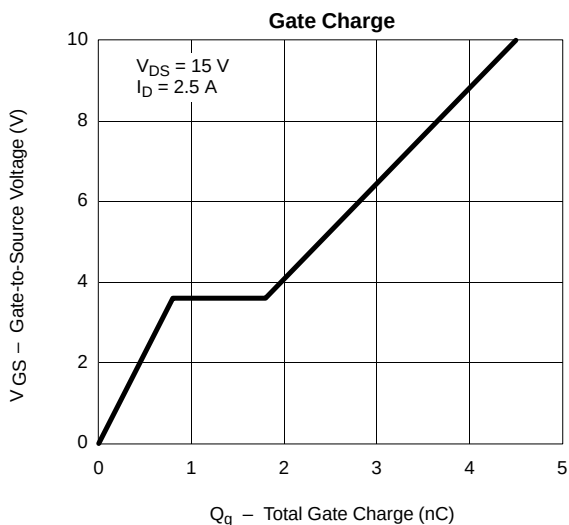
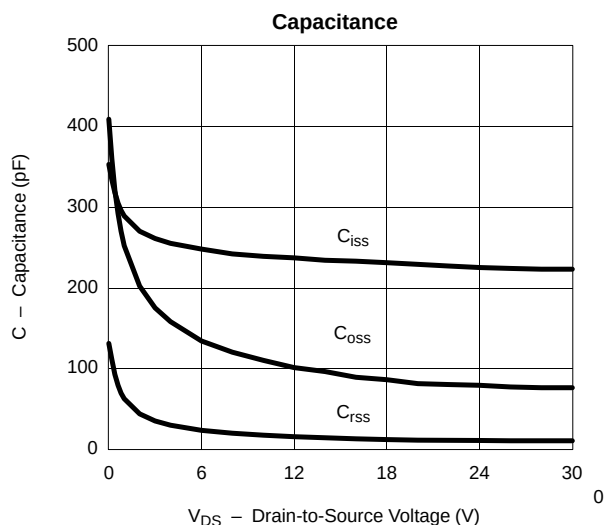
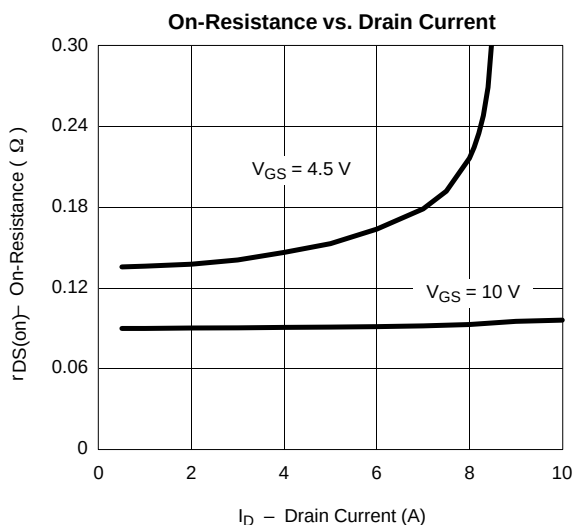
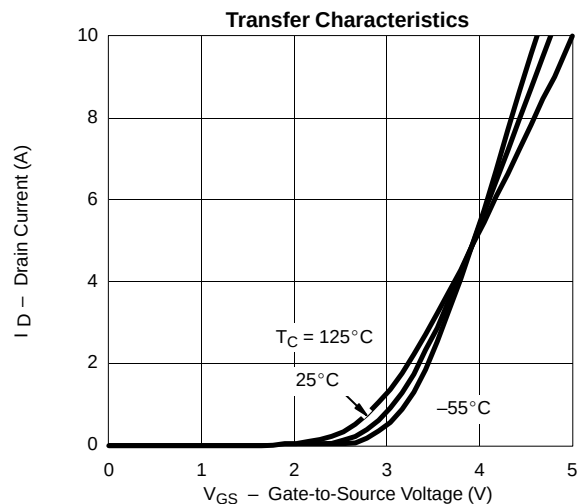
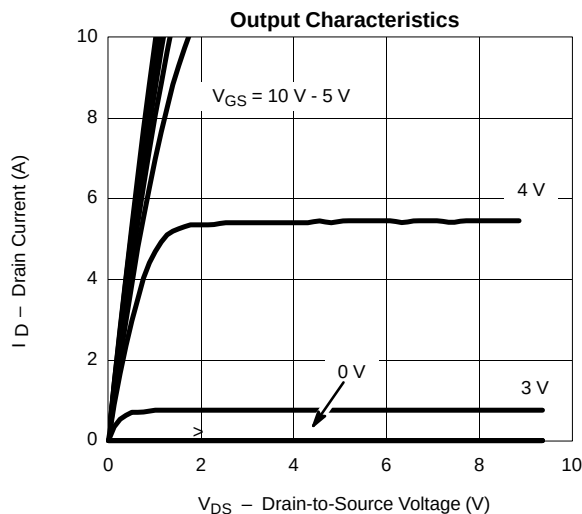
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			0.5	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			10	
		$V_{DS} = 30\text{ V}, V_{GS} = 1.0\text{ V}, T_J = 25^\circ\text{C}$			1	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 4.5\text{ V}, V_{GS} = 10\text{ V}$	6			A
		$V_{DS} \geq 4.5\text{ V}, V_{GS} = 4.5\text{ V}$	4			
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$		0.092	0.117	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 2.0\text{ A}$		0.142	0.190	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 4.5\text{ V}, I_D = 2.5\text{ A}$		4.6		S
Diode Forward Voltage	V_{SD}	$I_S = 1.25\text{ A}, V_{GS} = 0\text{ V}$		0.77	1.2	V
Dynamic						
Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 2.5\text{ A}$		2.4	4	nC
Total Gate Charge	Q_{gt}	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$		4.5	10	
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		240		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			17		
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\text{ }\Omega$		8	20	ns
Rise Time	t_r			12	30	
Turn-Off Delay Time	$t_{d(off)}$			17	35	
Fall-Time	t_f			8	20	

Notes

a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

